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# **Isc N-Channel MOSFET Transistor**

## TK20E60W5

Ros(C • Enhand Vth = 3 • 100% a • Minimu	PIRES ain-source on-resistance: $DN) = 175m\Omega$ (MAX) cement mode: B to 4.5V (VDS = 10 V, ID=1mA) avalanche tested im Lot-to-Lot variations for robust dev nance and reliable operation	Image: 1 2 3Image: Constrained by the second se		
<ul> <li>DESCF</li> <li>Switchi</li> </ul>	RITION ing Voltage Regulators			
• ABSOI	LUTE MAXIMUM RATINGS(Ta=25°C			
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	600	V	
V <sub>GS</sub>	Gate-Source Voltage	±30	V	
ID	Drain Current-Continuous	20	A	
Ідм	Drain Current-Single Pulsed	80	А	▲ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓
PD	Total Dissipation @Tc=25℃	165	W	DIM MIN MAX A 15.50 15.90 B 9.80 10.20
Тј	Max. Operating Junction Temperature	150	°C	C 4.20 4.50 D 0.70 0.90 F 3.40 3.70
T <sub>stg</sub>	Storage Temperature	-55~150	°C	G 4.98 5.18 H 2.68 2.90 J 0.44 0.60
• THERM	MAL CHARACTERISTICS	K         12.80         13.40           L         1.20         1.45           Q         2.70         2.90		
SYMBOL	PARAMETER	МАХ	UNIT	R         2.30         2.70           S         1.29         1.35
Rth(ch-c)	Channel-to-case thermal resistance	0.757	°C/W	U 6.45 6.65 V 8.66 8.86

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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA	600			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> =1mA	3		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =10A			175	mΩ
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V			±1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V			100	μA
VSDF	Diode forward voltage	I <sub>DR</sub> =20A, V <sub>GS</sub> = 0 V			1.7	V



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